電子電路設計模擬與實習

實驗名稱:數位電路

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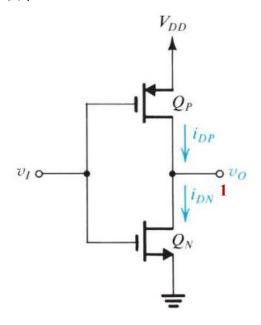
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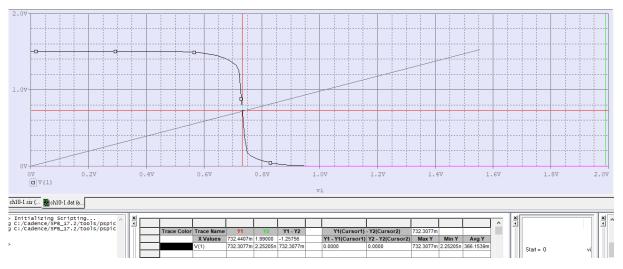
10. CMOS 主動負載差動放大器設計

Lab 10-1. CMOS 反向器 VTC 曲線模擬及靜態參數萃取實驗電路圖:

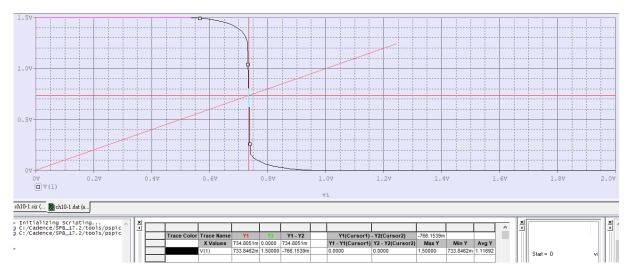


1. 模擬不同 λ(0.2、0.02、0.002)下之 VTC 曲線。

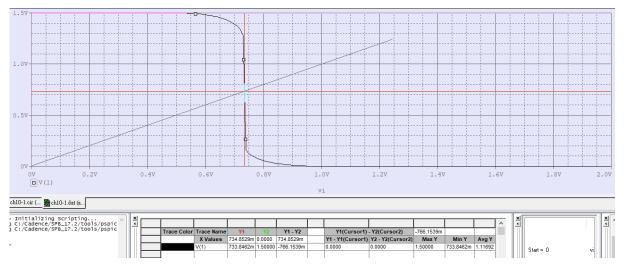
	λ		
	0.2	0.02	0.002
V_{M}	732. 4407m	734.8051m	734.8529m
g	-46. 1856	-11.1404	-8. 00048



 $\lambda = 0.2$



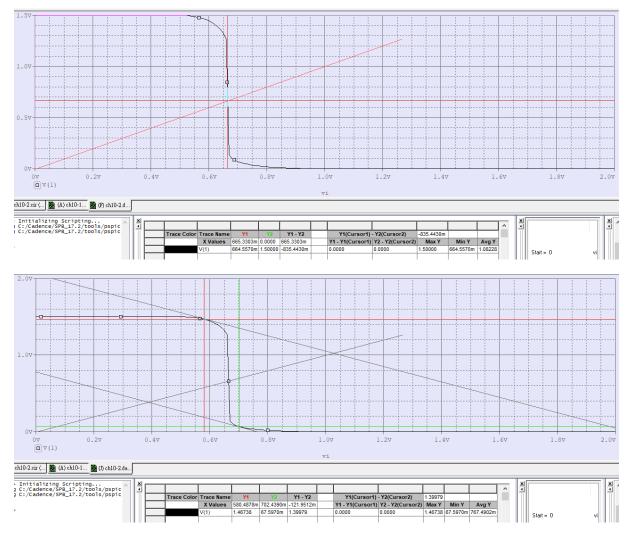
$\lambda = 0.02$



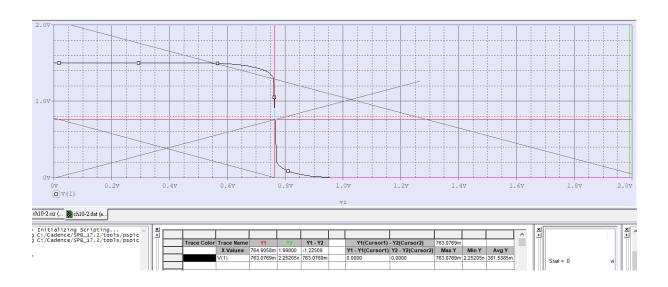
 $\lambda=0.\,002$

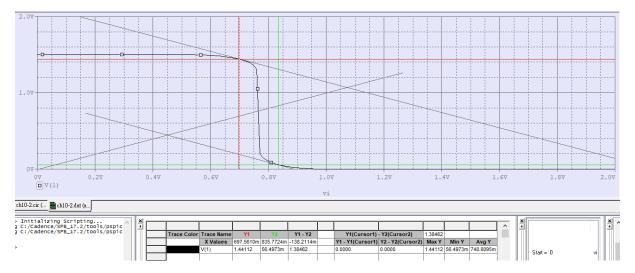
2. 模擬 PMOS、NMOS W/L 的尺寸比變動對反向器 VTC 曲線的影響。

静態變數	PMOS-to-NMOS ration			
	1	5	11	
V_{M}	665.3303m	764.9058m	814.6295m	
\boldsymbol{g}	-33. 3033	-406. 699	-14. 613	
V_{IL}	580. 4878m	697. 561m	773. 9837m	
V_{IH}	702.439m	835. 7724m	881.3008m	
V_{OL}	0	0	0	
V_{OH}	1.5	1.5	1.5	
NM_L	797. 561m	664. 2276m	618.6992m	
NM_H	580. 4878m	697. 561m	773. 9837m	

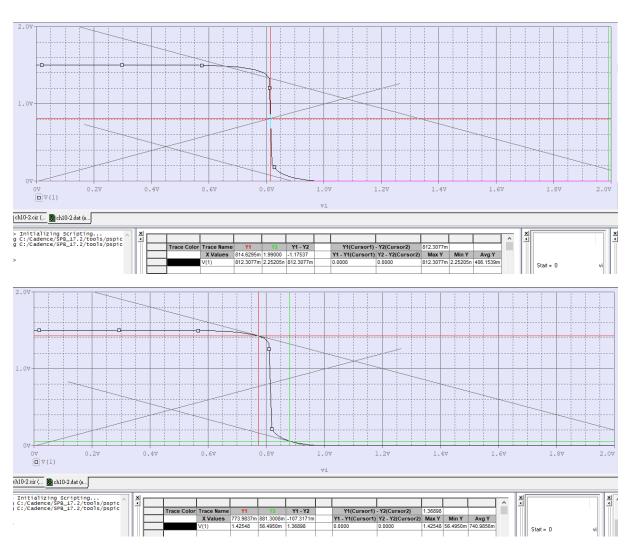


PMOS-to-NMOS ration = 1





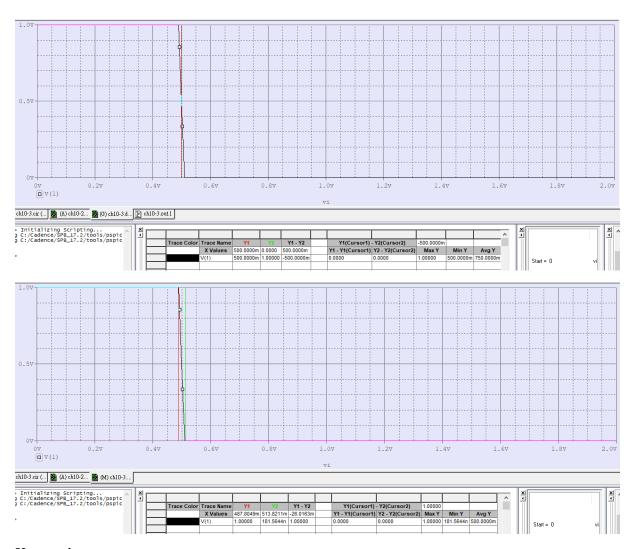
PMOS-to-NMOS ration = 5



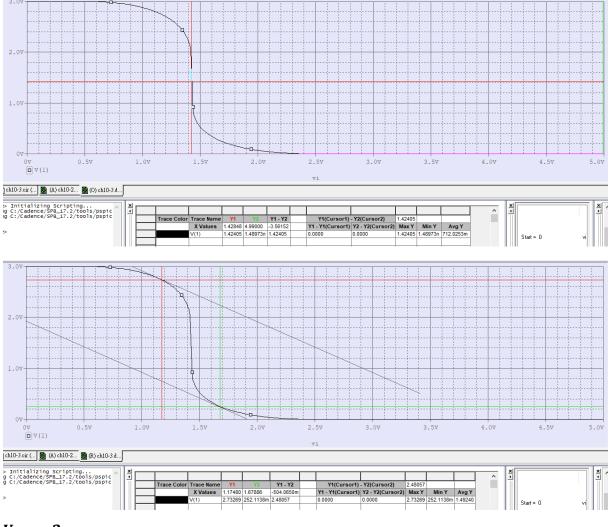
PMOS-to-NMOS ration = 11

3. 模擬電源電壓 VDD 變動對反向器 VTC 曲線的影響。

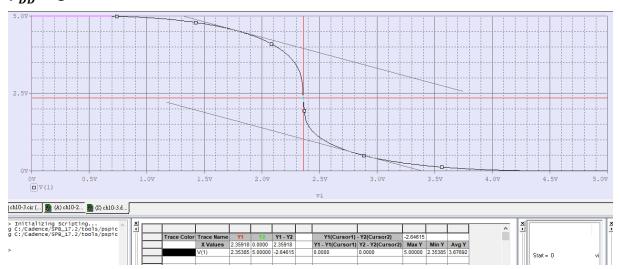
静態變數	V_{DD}			
	1	3	5	
V_{M}	0. 5	1. 42848	2. 35918	
g	0	-103. 479	-52. 6367	
V_{IL}	487.8049m	1.17480	1.83058	
V_{IH}	513.8211m	1. 67886	2. 85950	
V_{OL}	0	0	0	
V_{OH}	1	3	5	
NM_L	486.1789m	1. 32114	2. 14050	
NM _H	487.8049m	1. 17480	1. 83058	

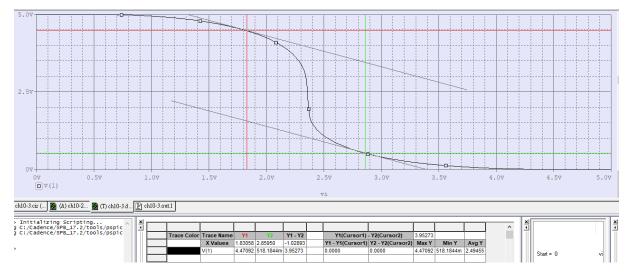


 $V_{DD} = 1$



$V_{DD}=3$





 $V_{DD}=5$